



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.: 10/780,031 Confirmation No.: 9275
First Named Inventor: Park, Jongmin Filing Date: 17 February 2004
Group Art Unit: 2824 Examiner: Wendler, Eric J.
Atty. Docket No.: R-0003 US
Title: Technique for Programming Floating-gate Transistor Used in
Circuitry Such as Flash EPROM
Assignee(s): ProMOS Technologies Inc.

Mountain View, California
18 July 2006

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RESPONSE TO OBJECTION TO DRAWINGS

Sir:

This is a response to the objection to the drawings presented in the Notice of Allowability mailed 19 April 2006 for the above patent application.

On page 2 of the Notice of Allowability, the Examiner asserts that "The drawings are objected to as failing to comply with 37 CFR 1.84(p)(5) because they do not include the following reference sign(s) mentioned in the description: V_{SPH} paragraph 0052; V_{CEL} , paragraph 0057; V_{CPH} , paragraph 0058; V_{SRF} , V_{SPT} , paragraph 0064; V_{CRF} , V_{CPT} , paragraph 0065; V_{ITM} , paragraph 0069; and V_{BEH} , paragraph 0072". This objection is respectfully traversed.

Reference symbols V_{SPH} , V_{CPH} , V_{ITM} , and V_{BEH} respectively represent the high values of voltage signals V_{SP} , V_{CP} , V_{SG} , and V_{BE} which appear in the circuit diagrams of Figs. 1 and 2. Reference symbols V_{SPT} and V_{CPT} respectively represent target values of high values V_{SPH} and V_{CPH} which, as just mentioned, respectively represent the high values of voltage signals V_{SP} and V_{CP} that appear in Figs. 1 and 2. Reference symbol V_{SRF} and V_{CRF} respectively represents source-voltage percentage-target-reference voltages that exceed nominal value V_{SS}

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by respective specified percentages of the voltage distances from nominal value V_{SS} to respective target values V_{SPT} and V_{CPT} of respective high values V_{SPH} and V_{CPH} . Reference symbol V_{CEL} represents the low value of voltage signal V_{CE} which appears in the circuit diagrams of Figs. 1 and 2.

37 CFR 1.84(p)(5) specifies that "Reference characters not mentioned in the description shall not appear in the drawings" and that "Reference characters mentioned in the description must appear in the drawings". The Examiner seems to have interpreted the second provision of 37 CFR 1.84(p)(5) to mean that all reference symbols (or signs) which appear in the specification must appear in the drawings. However, the specifications of U.S. patents and patent applications commonly contain reference symbols which do not appear in the drawings. For example, reference symbols used in equations presented in the specifications of U.S. patents and patent applications commonly do not appear in their drawings. Similarly, as in the present situation, reference symbols representing the values of items described in the specifications of U.S. patents and patent applications commonly do not appear in the drawings.

It is the understanding of Applicant's Attorney that the second provision of 37 CFR 1.84(p)(5) means that all reference symbols representing items shown in the drawings of U.S. patents and patent applications must appear in those drawings. The corollary of this is that reference symbols representing items not shown in the drawings of U.S. patents and patent applications should not appear in those drawings. Inasmuch as the specifications of U.S. patents and patent applications commonly contain reference symbols which do not appear in their drawings, Applicant's Attorney's understanding of the second provision of 37 CFR 1.84(p)(5) seems to be the generally understood interpretation of that provision.

As mentioned above, reference symbols V_{CEL} and V_{BEH} represent certain values of the voltages respectively represented by reference symbols V_{CE} and V_{BE} which appear in Figs. 1 and 2 while reference symbols V_{SRF} , V_{SPT} , V_{CRF} , and V_{CPT} are variously related to the high values V_{SPH} and V_{CPH} of the voltages represented by reference symbols V_{SP} and V_{CP} that appear in Figs. 1 and 2. However, none of reference symbols V_{CEL} , V_{SRF} , V_{SPT} , V_{CRF} , V_{CPT} , and V_{BEH} represents an item shown in Fig. 1, in Fig. 2, or in any of the other drawings. Accordingly, none of reference symbols V_{CEL} , V_{SRF} , V_{SPT} , V_{CRF} , V_{CPT} , and V_{BEH} should appear in any of the drawings. Inasmuch as none of reference symbols V_{CEL} , V_{SRF} , V_{SPT} ,

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V_{CRF} , V_{CPT} , and V_{BEH} do appear in any of the drawings, the drawings comply with 37 CFR 1.84(p)(5) with respect to reference symbols V_{CEL} , V_{SRF} , V_{SPT} , V_{CRF} , V_{CPT} , and V_{BEH} .

As also mentioned above, reference symbols V_{SPH} , V_{CPH} , and V_{ITM} represent the high values of the voltages represented by reference symbols V_{SP} , V_{CP} , and V_{SG} that appear in Figs. 1 and 2. However, none of reference symbols V_{SPH} , V_{CPH} , and V_{ITM} represents an item shown in Fig. 1 or 2. Consequently, none of reference symbols V_{SPH} , V_{CPH} , and V_{ITM} should appear in Fig. 1 or 2.

Reference symbols V_{SPH} , V_{CPH} , and V_{ITM} do appear in the graphs of Figs. 4 - 13 because those three reference symbols represent voltage levels appearing in Fig. 4 - 13. Since reference symbols V_{SPH} , V_{CPH} , and V_{ITM} appear in Figs. 4 - 13 where those three reference symbols should appear and do not appear in any of the other figures (including Figs. 1 and 2) where those three reference symbols should not appear, the drawings comply with 37 CFR 1.84(p)(5) with respect to reference symbols V_{SPH} , V_{CPH} , and V_{ITM} .

In short, the drawings fully comply with 37 CFR 1.84(p)(5) with respect to all of reference symbols V_{SPH} , V_{CEL} , V_{CPH} , V_{SRF} , V_{SPT} , V_{CRF} , V_{CPT} , V_{ITM} , and V_{BEH} cited in the objection to the drawings. Hence, the objection to the drawings should be withdrawn.

Please telephone Attorney for Applicant(s) at 650-964-9767 if there are any questions.

EXPRESS MAIL LABEL NO.:

EV 743 585 224 US

Respectfully submitted,



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SUBMISSION OF FORMAL DRAWINGS

Sir:

Enclosed for the above patent application are nine sheets of replacement formal drawings consisting of Figs. 1 - 17. The enclosed drawings incorporate the revisions requested in the accompanying Amendment to Drawings. If these revisions are acceptable, please substitute the enclosed drawings for the informal drawings now on file.

Please telephone Attorney for Applicant(s) at 650-964-9767 if there are any questions regarding these drawings.

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